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ABSTRACT

5 An electronic device material comprising at least an
electronic device substrate and a silicon oxynitride film
disposed on the substrate is provided. The silicon
oxynitride film is characterized by containing nitrogen
atoms in a large amount in the vicinity of the oxynitride
film surface when the nitrogen content distribution in
the thickness direction of the silicon oxynitride film is
10 examined by SIMS (secondary ion mass spectrometry)
analysis. By virtue of this constitution, an electronic
device material comprising an oxynitride film having an
excellent effect of preventing penetration of boron and
having excellent gate leak properties can be obtained.